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Sheet 1 of 1

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| Substitute Form PTO-1449 (Modified) | U.S. Department of Commerce Patent and Trademark Office | Attorney's Docket No. 12406-018001 | Application No. |
| Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b)) | | Applicant Martin Behringer et al. | |
| | | Filing Date Herewith | Group Art Unit |

U.S. Patent Documents

| Examiner Initial | Desig. ID | Patent Number | Issue Date | Patentee | Class | Subclass | Filing Date If Appropriate |
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| <i>SR</i> | AA | 5,396,103 | 03/07/1995 | OIU et al. | | | |
| | AB | | | | | | |
| | AC | | | | | | |
| | AD | | | | | | |
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Foreign Patent Documents or Published Foreign Patent Applications

| Examiner Initial | Desig. ID | Document Number | Publication Date | Country or Patent Office | Class | Subclass | Translation | |
|------------------|-----------|-----------------|------------------|--------------------------|-------|----------|-------------|----|
| | | | | | | | Yes | No |
| | AJ | | | | | | | |
| | AK | | | | | | | |
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| | AN | | | | | | | |

Other Documents (include Author, Title, Date, and Place of Publication)

| Examiner Initial | Desig. ID | Document |
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| <i>SR</i> | AO | Magnea, N., "ZnTe fractional monolayers and dots in a CdTe matrix" 6 th International Conference on II-VI Compounds and related optoelectric materials, Journal of Crystal Growth, 138 (1994): 550-558. |
| <i>SR</i> | AP | Kutzer, V. et al., "Gain to absorption conversion by increasing excitation density in excitonic waveguides", Journal of Crystal Growth, 184/185 (1998): 632-636. |
| <i>SR</i> | AQ | Faschinger, W. et al., "Processes occurring during the formation of graded ZnSe/ZnTe contacts on p-ZnSe", Semicond. Sci. Technol., 12 (1997): 1291-1297. |
| <i>SR</i> | AR | Hirose, J. et al., "p-type conductivity control of ZnSe with insertion of ZnTe:Li submonolayers in metalorganic molecular-beam epitaxy", Journal of Applied Physics, 84 (01 DEC 1998): 6100-6104. |
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| Examiner Signature <i>Shousun Lee</i> | Date Considered <i>2/1/05</i> |
| EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |